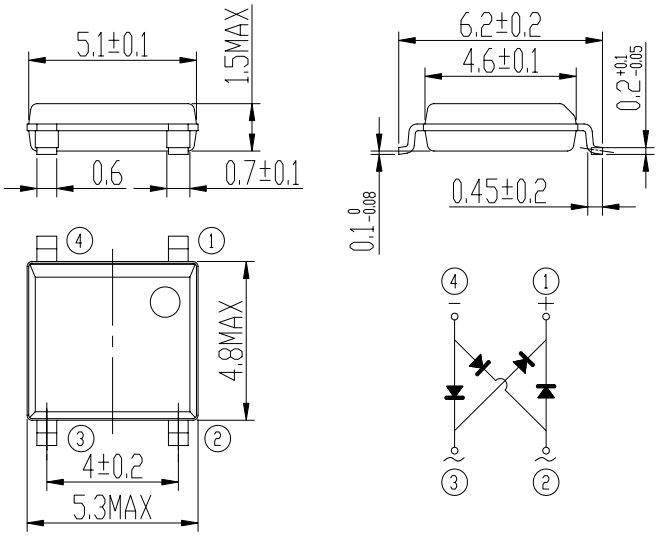
LB2S thru LB10S

Reverse Voltage 200 and 1000V Forward Current 1.0A



Features

- ◆ Low Profile: Typical height of 1.4mm
- ◆ Ideal for automated placement
- ◆ High surge current capability
- ◆ Solder Dip 260°C，40seconds

Mechanical Data

- ◆ Case:SOPA-4
  Epoxy meets UL-94V-0 Flammability rating
- ◆ Terminals:Matte tin plated ldads, solderable per
  J-STD-002B and JESD22-B102D
- ◆ Polarity:As markde on body

Maximum Ratings & Electrical Characteristics Ratings at 25°C

Parameter	Symbol	LB2S	LB4S	LB6S	LB8S	LB10S	Unit
Maximum repetitive peak reverse voltage	RRM	200 V	400	600	800	1000	V
Maximum RMS voltage	VRMS	140	280	420	560	800	V
Maximum DC blocking voltage	VDC	200	400	600	800	1000	V
Maximum Average forward output rectified current on glass-eposy P.C.B on aluminum substrate	IF(AV)	1.0 0.8					A
Peak forward surge current 8.3 ms single sine-wave superimposed on rated load (JEDEC Method)	IFSM	30					A
Rating for fusig (t<8.3ms)	i²t	3					A²sec
Maximum instantaneous forward voltage drop per diode at 0.4A	VF	0.95					V
Maximum DC reverse current at TA=25 rated DC blocking voltage per leg TA=125	IR	5 500					μA
Typical thermal resistance per leg (Note 1)	RθJA RθJL	80 25					°C/W
Operating junction temperature range	TJ	-55 to +150					°C °C
Storage temperature range	TSTG	-55 to +150					

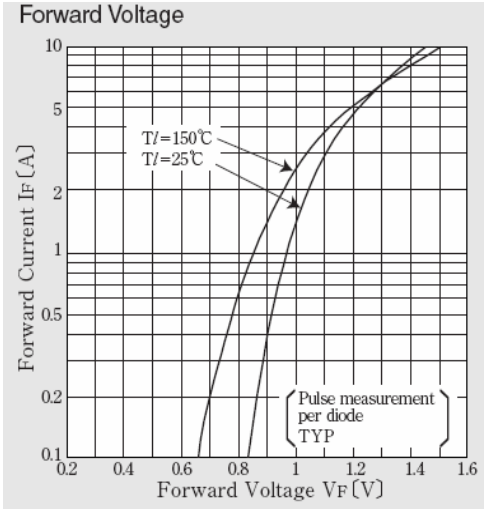
Notes: 1. Device mounted P.C.B with 0.47x0.47"(12mmx12mm) Copper Pads.
2. JEDEC registered values

Reverse Voltage 200 and 1000V Forward Current 1.0A

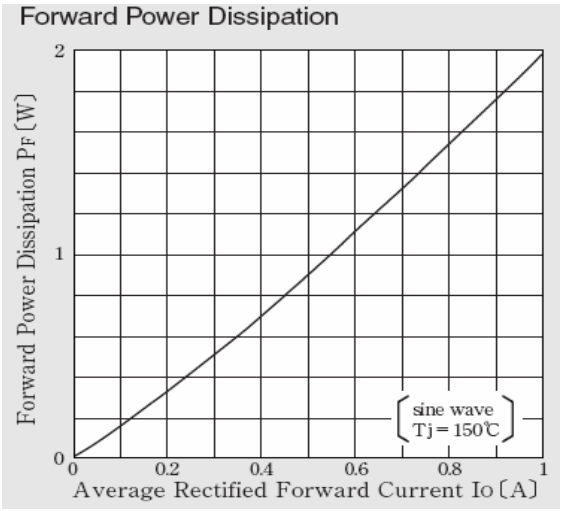
RATINGS AND CHARACTERISTIC CURVES

(TA=25℃ unless ontherwise noted)

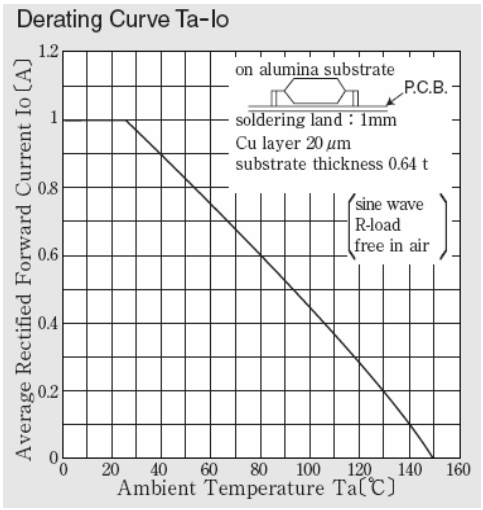
Forward Voltage



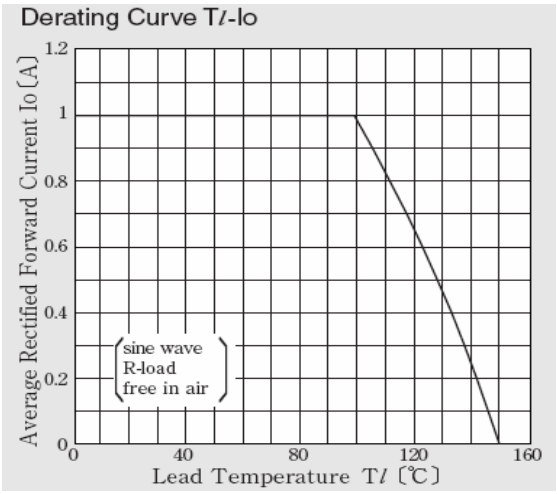
Forward Power Dissipation



Derating Curve Ta-Io



Derating Curve TJ-Io



Peak Surge Forward Current Capability